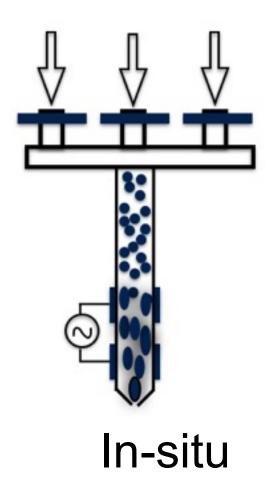
Atmospheric Pressure Plasma Jet as a Dry Alternative to Inkjet Printing in Flexible Electronics

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Abstract

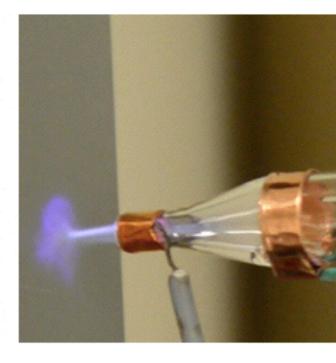
We have developed an atmospheric pressure plasma jet printing system that works at room temperature to 50 deg C unlike conventional aerosol assisted techniques which require a high temperature sintering step to obtain desired thin films. Multiple jets can be configured to increase throughput or to deposit multiple materials, and the jet(s) can be moved across large areas using a x-y stage. The plasma jet has been used to deposit carbon nanotubes, graphene, silver nanowires, copper nanoparticles and other materials on substrates such as paper, cotton, plastic and thin metal foils.

Plasma Jet Multi-Material Printer





Plasma Off



Plasma On

-20sec __ 60sec 90sec

Wave number (cm⁻¹)

Low & High K Dielectric Coating

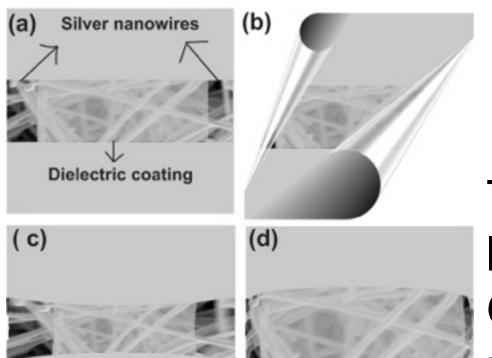
tailoring/printing

In-line additive manufacturing

- •Nanocolloids, organic materials etc. transported as aerosol by carrier gas
- Precise control over thickness and morphology
- •Ability to tailor material properties in situ (chemical, electronic)
- •Can be combined as an in-line manufacturing process in additive manufacturing

Silicon di oxide coating

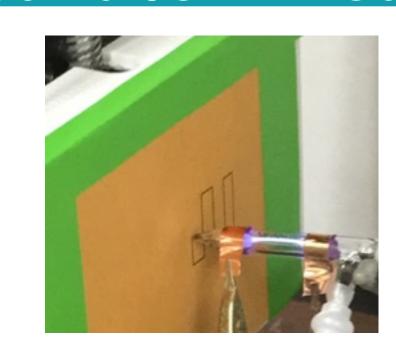
Wave number (cm⁻¹)

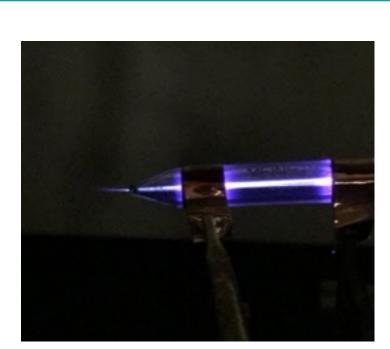


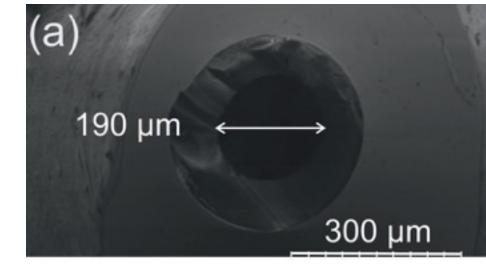
Nitrogen-incorporated silicon oxide coating

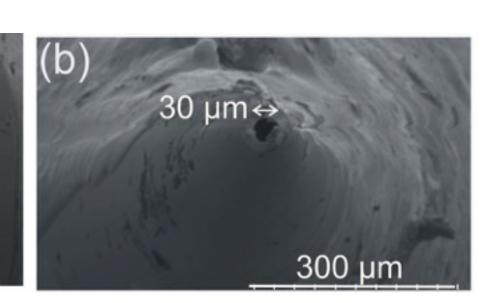
Thin gate dielectric, passivation layer in microelectronics Optical waveguides (varying refractive index)

Plasma Jet Printed Electronics





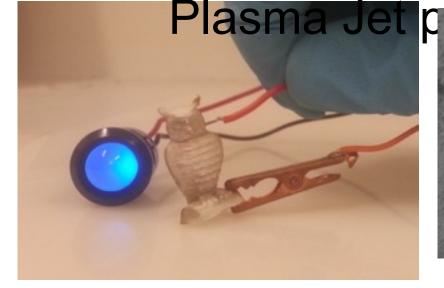




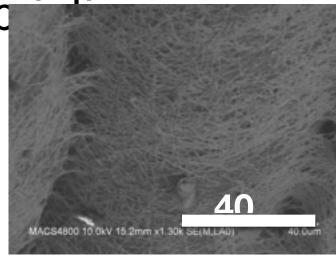
Scanning electron microscopic image of Nozzle antenna structure

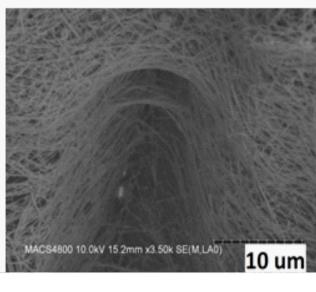
Plasma printed

on PET bottle



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Silver nanowires on 3D printed ABS plastic

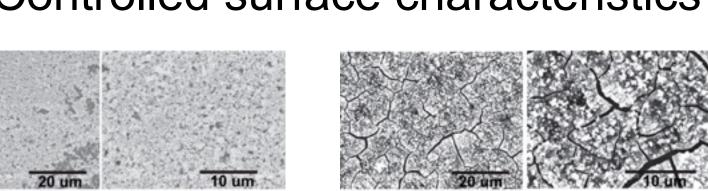
Copper on poly imide

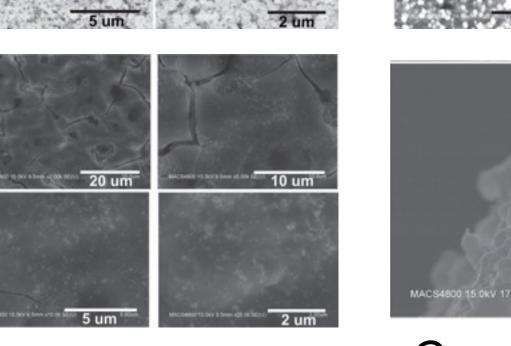
On paper

On PET bottle

In-situ Tailoring of Material Properties

In-situ reduction of Cu2+ to metallic copper 60000 50000 40000 € 30000 gg 20000 10000 960 Cu L edge XAS^{mono} No post processing, No pre-post thermal treatment Printed using same colloid





2 um

Cross sectional SEM of Cu(1) on Silicon(2)

Controlled surface characteristics Contacts & Reference

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(1)Three US Patent applications pending

- Ram P. Gandhiraman et al., Applied Physics Letters. **2016**, 108, 123103.
- (3) Ram P. Gandhiraman et al., ACS Appl Mater Interfaces. **2014**, 6, 20860
- (4)Ram P. Gandhiraman, Dennis Nordlund, Vivek Jayan, M. Meyyappan, Jessica E. Koehne. ACS Appl Mater Interfaces. 2014, 6, 22751.
- (5)<u>https://www.sciencedaily.com/releases/</u> 2016/03/160322120038.htm